



# DCR590G65

# **Phase Control Thyristor**

Replaces DS5870-4 DS5870-5 July 2020 (LN40121)

#### **FEATURES**

- Double Side Cooling
- High Surge Capability

#### **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

### **VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages VDRM and VRRM (V)	Conditions
DCR590G65* DCR590G60 DCR590G55	6500 6000 5500	$T_{Vj} = -40 ^{\circ} C$ to 125 $^{\circ} C$ , $IDRM = IRRM = 100 mA$ , $VDRM$ , $VRRM$ tp = 10 ms $VDSM \& VRSM = VDRM \& VRRM + 100 V$ respectively

Lower voltage grades available.

#### **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

#### DCR590G65

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

#### **KEY PARAMETERS**

$V_{DRM}$	6500V
I <sub>T(AV)</sub>	595A
Ітѕм	6600A
dV/dt*	1500V/µs
dl/dt	200A/μs

<sup>\*</sup> Higher dV/dt selections are available

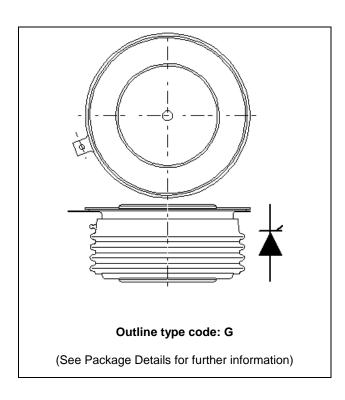


Fig. 1 Package outline

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<sup>\*6200</sup>V @ -40°C, 6500V @ 0°C



# **CURRENT RATINGS**

# T<sub>case</sub> = 60°C unless stated otherwise

Symbol	Parameter Test Conditions		Max.	Units
Double Si	de Cooled			
IT(AV)	Mean on-state current	Half wave resistive load	595	А
IT(RMS)	RMS value	-	935	А
lτ	Continuous (direct) on-state current	-	912	А

# **SURGE RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, Tcase = 125°C	6.6	kA
l²t	I <sup>2</sup> t for fusing	V <sub>R</sub> = 0	0.22	MA <sup>2</sup> s

# THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Condition	Min.	Max.	Units	
		Double side cooled	DC	-	0.0268	°C/W
Rth(j-c)	Thermal resistance - junction to case	Cingle side and a	Anode DC	-	0.0527	°C/W
		Single side cooled	Cathode DC	-	0.0652	°C/W
Davis	The second resistance and the best-interest	Clamping force 11.5kN	Double side	-	0.0072	°C/W
Rth(c-h)	Thermal resistance - case to heatsink	(with mounting compound)	Single side	-	0.0144	°C/W
Tvj	Virtual junction temperature	Blocking Vdrm / Vrrm		-	125	°C
Tstg	Storage temperature range			-55	125	°C
Fm	Clamping force			10	13	kN

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# **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Condition	ıs	Min.	Max.	Units
IRRM/IDRM	Peak reverse and off-state current	At VRRM/VDRM, Tcase = 125°C	;	-	100	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% VdRM, Tj = 125°C, ga	ate open	-	1500	V/µs
		From 67% VDRM to 2x IT(AV)	Repetitive 50Hz	-	100	A/µs
dl/dt	Rate of rise of on-state current	Gate source 30V, 10Ω	Non-repetitive	-	200	A/µs
		tr < 0.5µs, Tj = 125°C				
Vezes	Threshold voltage - Low level	100A to 400A at Tcase = 125	5°C	-	0.912	V
<b>V</b> T(TO)	Threshold voltage - High level	400A to 1600A at Tcase = 12	25°C	-	1.108	V
_	On-state slope resistance - Low level	100A to 400A at Tcase = 125°C		-	2.157	mΩ
ľτ	On-state slope resistance - High level	400A to 1600A at Tcase = 125°C		-	1.647	mΩ
	Delaysting	VD = 67% VDRM, gate source 30V, 10Ω			0	
tgd	Delay time	tr = 0.5µs, Tj = 25°C		-	3	μs
	Town off the	$T_j = 125$ °C, $V_R = 100$ V, $dI/dt = 5$ A/ $\mu$ s,		550	4400	
tq	Turn-off time	It = 500A, dVpr/dt = 20V/µs linear		550	1100	μs
Qs	Stored charge	L 500A T: 40500 dl/dt 5A/		1800	2600	μC
IRR	Reverse recovery current	- Iτ = 500A, Tj = 125°C, dl/dt = 5A/μs		77	90	А
Iι	Latching current	Tj = 25°C, VD = 5V		-	3	Α
lн	Holding current	Tj = 25°C, Rg-κ = ∞, Iτм = 50	0A, Ιτ = 5A	-	300	mA

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### **GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	DI Parameter Test Conditions		Max.	Units
<b>V</b> GT	Gate trigger voltage	VDRM = 5V, Tcase = 25°C	1.5	V
<b>V</b> GD	Gate non-trigger voltage	At 50% VDRM, Tcase = 125°C	0.4	V
lgт	Gate trigger current	VDRM = 5V, Tcase = 25°C	350	mA
Igp	Gate non-trigger current	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	10	mA

### **CURVES**

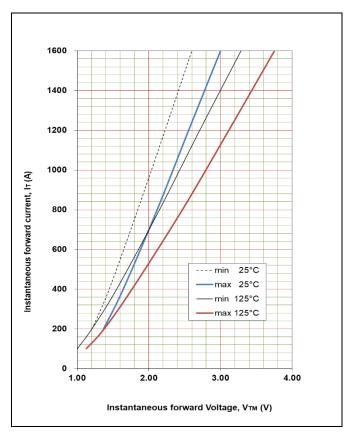


Fig. 2 Maximum & minimum on state characteristics

# **VTM EQUATION**

 $V_{TM} = A + B.In(I_T) + C.I_T + D.\sqrt{I_T}$ 

Where A = 0.542452

B = 0.065613

C = 0.001318

D = 0.015356

These values are valid for  $T_j = 125$ °C for  $I_T 100$ A to 1600A

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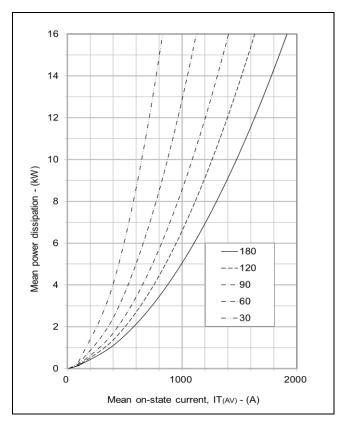


Fig. 3 On-state power dissipation - sine wave

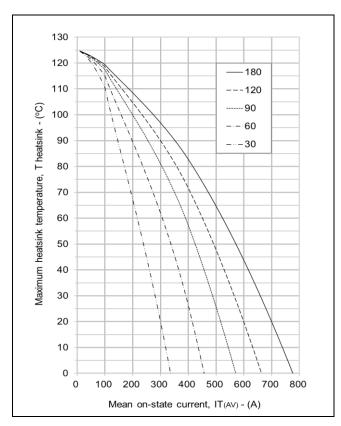


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

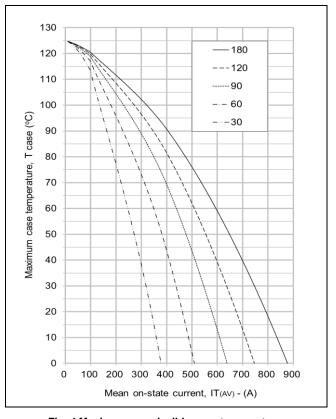


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

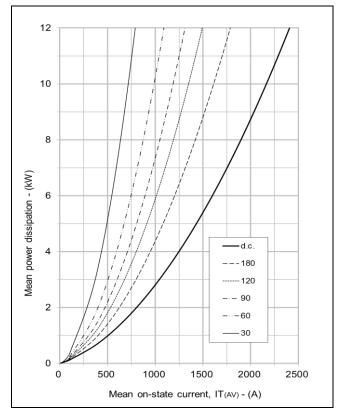


Fig. 6 On-state power dissipation - rectangular wave

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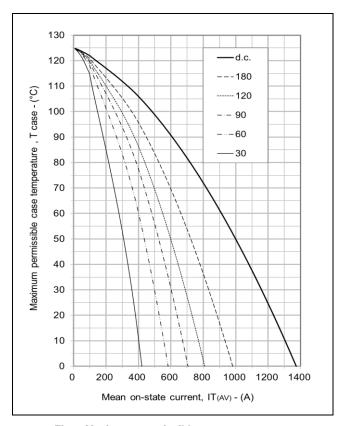
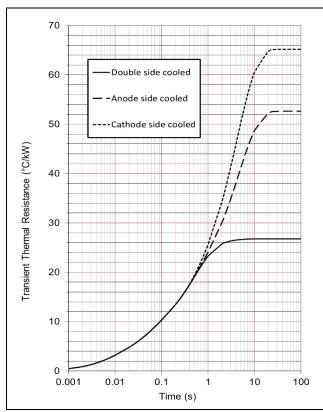


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



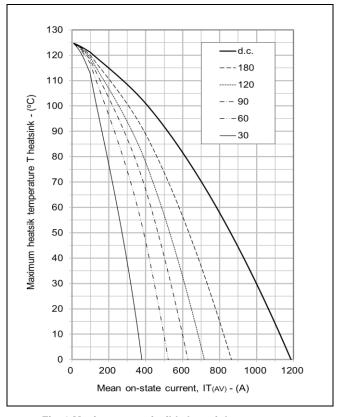


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side	Ri(°C/kW)	2.2995	5.4226	16.9074	2.1488
cooled	Ti(s)	0.0066401	0.0457025	0.4962482	1.8248
Anode side	Ri(°C/kW)	2.3214	5.2661	10.2686	34.8031
cooled	Ti(s)	0.0066948	0.045528	0.3484209	4.582
Cathode side	Ri(°C/kW)	2.4895	5.9105	7.4256	49.3432
cooled	Ti(s)	0.0070404	0.052895	0.3933903	4.2295

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

 $\Delta R_{\text{th(j-c)}}$  Conduction

Tables show the increments of thermal resistance R  $_{\text{th}(j-c)}$  when the device operates at conduction angles other than d.c.

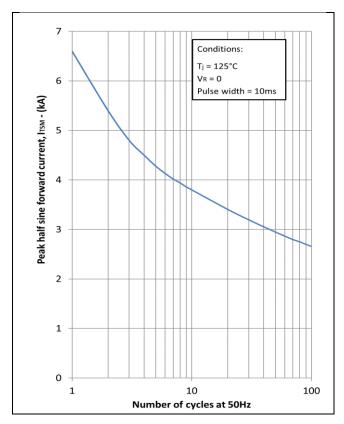
	Double side co	oling			Anode Side	Cooling
	ΔZ <sub>th</sub> (	(z)			$\Delta Z_i$	h (Z)
6°	sine.	rect.		θ°	sine.	rect.
180	4.15	2.72		180	4.15	2.72
120	4.90	4.02		120	4.89	4.02
90	5.74	4.79		90	5.73	4.78
60	6.53	5.65		60	6.52	5.65
30	7.16	6.64		30	7.15	6.62
15	7.46	7.18	1	15	7.44	7.16

Ca	thode Sided Cooling				
	$\Delta Z_{t}$	$\Delta Z_{th}(z)$			
θ°	sine.	rect.			
180	4.13	2.71			
120	4.87	4.00			
90	5.69	4.76			
60	6.46	5.60			
30	7.07	6.56			
15	7.36	7.09			

Fig. 9 Maximum (limit) transient thermal impedance – junction to case (degC/kW)

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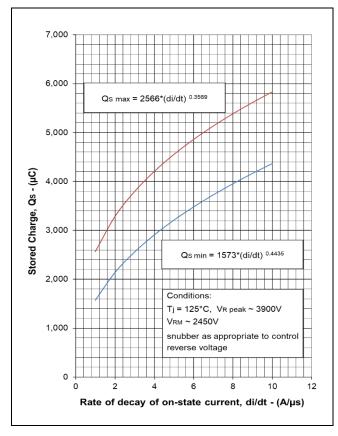


Fig. 12 Reverse recovery charge

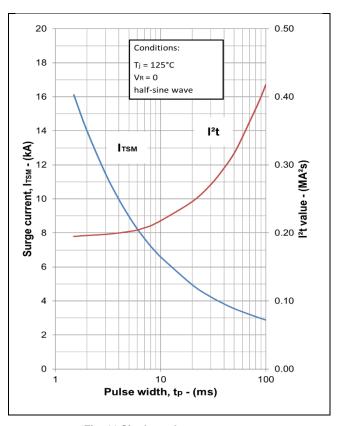


Fig. 11 Single-cycle surge current

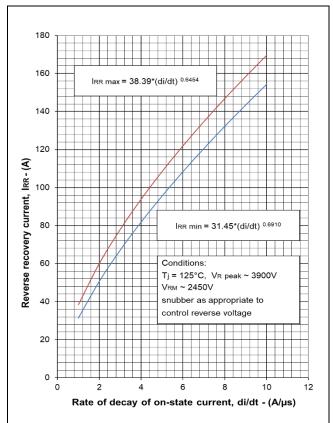


Fig. 13 Reverse recovery current

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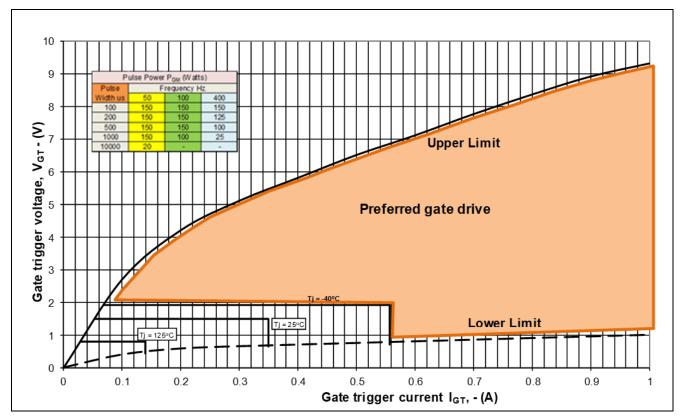


Fig. 14 Gate characteristics

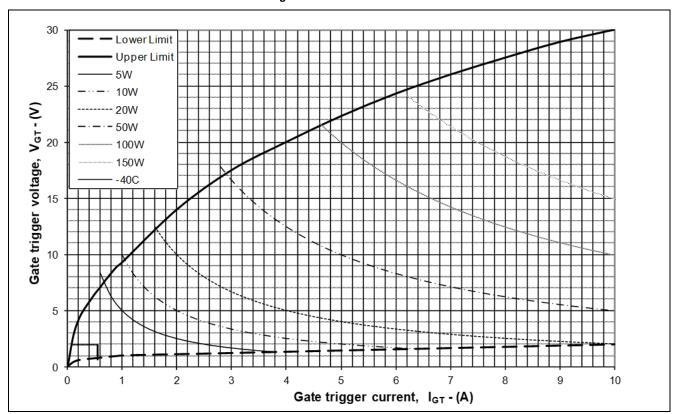


Fig. 15 Gate characteristics

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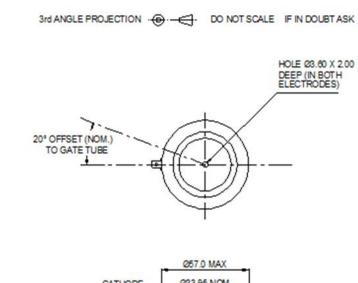


# **PACKAGE DETAILS**

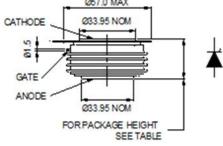
For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE



	Maximum	Minimum
	Thickness	Thickness
Device	(mm)	(mm)
DCR470G85	27.4	26.9
DCR590G65	27.1	26.6
DCR690G52	26.9	26.3
DCR780G42	26.7	26.2
DCR960G28	26.5	26.0
DCR1080G22	26.4	25.9



Clamping force: 10 - 13kN

Lead length: 420mm

Lead terminal connector: M4 ring

Package outline type code: G

Fig. 16 Package outline

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